

OPA5625H

High Bright

Standard Green LED Chip

GaP / GaP

1. Material Substrate GaP (N Type)
Epitaxial Layer GaP (P/N Type)

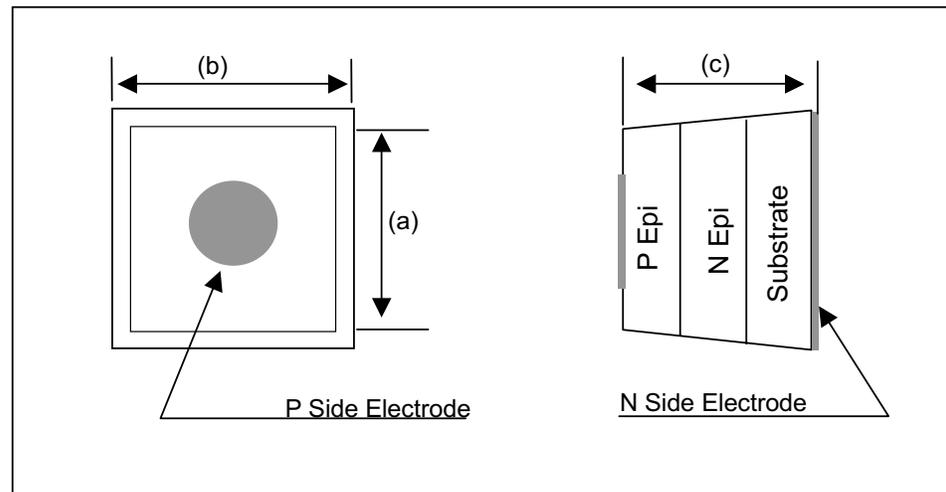
2. Electrode N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.8		V	$I_F=1\text{mA}$
	$V_{F(2)}$		2.2	2.5	V	$I_F=20\text{mA}$
Reverse Voltage	V_R	6.0			V	$I_R=10\mu\text{A}$
Brightness	I_V	500	650		mcd	$I_F=20\text{mA}$
Wavelength	Hue		567		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		26		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1³/₄ plastic package.

4. Mechanical Data (a) Emission Area ----- 12mil × 12mil
(b) Bottom Area ----- 14mil × 14mil
(c) Chip Thickness ----- 11mil



Knowledge*on Inc.

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